

**REMARKS**

The above amendment with the following remarks is submitted to be fully responsive to the Office Action of August 17, 2006. Reconsideration of this application in light of the amendment and the allowance of this application are respectfully requested.

Claims 1-24 are pending, of which claims 4-9 are presently withdrawn from consideration in the present application prior to the above amendment. Therefore, claims 1-3 and 10-24 are still pending in the present application and are believed to be in proper condition for allowance.

**Rejection under 102(b) over Muragishi**

Referring now to the Office Action, claims 1, 11-16, 18, and 21-24 are rejected under 35 U.S.C. 102(b) as being anticipated by Muragishi (US Patent No. 5,436,184), newly cited. Applicants respectfully traverse.

Muragishi is generally directed to a method of producing TFTs. In the method, a channel forming region 15d is formed in the active layer. The reference numeral 15f appears to be a junction region of the channel forming region 15d and source/drain regions 15e, which should be distinguished from the channel forming region 15d. (See col. 12, lines 46-49.)

In contrast, the present invention of independent claims 1 and 11-16 recite a semiconductor device having “a channel forming region formed in the active layer and between the source and drain regions, wherein a portion of the channel forming region is convexed or concaved in a channel width direction, which is parallel to a plane of the substrate”. The channel forming region 15d of Muragishi is not convexed or concaved. Because Muragishi does not describe a concave or convexed channel forming region, as is recited in independent claims 1 and 11-16, Applicants respectfully submit that Muragishi does not anticipate claims 1 and 11-16. Accordingly, Applicants respectfully request this rejection be withdrawn.

Dependent claims 18 and 21-24 depend from independent claims 1, 11, 12, 13, and 14, respectively, and are therefore allowable at least for the aforementioned reasons, and further for the additional features recited.

Rejection under 103(a) over Muragishi in view of Japanese patent [4]04152676A

Claims 2, 3, 19, and 20 are rejected under 35 U.S.C. 103(a) as being unpatentable over Muragishi as applied to claim 1 above, and further in view of the Japanese patent [4]04152676A previously cited. Applicants respectfully traverse.

As above, Applicant notes that Muragishi describes a channel forming region 15d, formed in the active layer. The reference numeral 15f is a junction region of the channel forming region 15d and source/drain regions 15e, which should be distinguished from the channel forming region 15d. (See col. 12, lines 46-49.) In contrast, the present independent claims 2 and 3 recite “a channel forming region formed in the active layer and between the source and drain regions, wherein a portion of the channel forming region is convexed or concaved in a channel width direction, which is parallel to a plane of the substrate”.

Examiner has additionally cited Japanese patent [4]04152676A in rejecting claims 2, 3, 19, and 20. Japanese patent [4]04152676A is generally directed to a method of fabricating a TFT but does not overcome the deficiency of Muragishi discussed above and as is recited in independent claims 2 and 3. Thus, the addition of Japanese patent [4]04152676A does not cure the defects of Muragishi.

Thus, neither Muragishi nor Japanese patent [4]04152676A, alone or in combination, teach or suggest a concave or convexed channel forming region, as is recited in independent claims 2 and 3. Accordingly, Applicant respectfully submits that Muragishi nor Japanese patent [4]04152676A do not render claims 2 and 3 unpatentable, and that this rejection be withdrawn.

Dependent claims 19 and 20 dependent from independent claims 2 and 3, respectively, and are therefore allowable at least for the aforementioned reasons, and further for the additional features recited.

Rejection under 103(a) over Muragishi in view of Japanese patent 2001028338

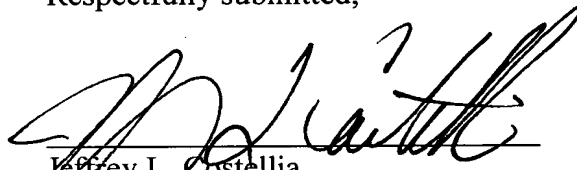
Claims 10 and 17 are rejected under 35 U.S.C. 103(a) as being unpatentable over the Muragishi, as applied to claims 1 and 16 above, and further in view of the Japanese patent 2001028338, previously cited.

Dependent claims 10 and 17 dependent from independent claims 1 and 3 and 11-16, respectively, and are therefore allowable at least for the aforementioned reasons, and further for the additional features recited.

Conclusion

In view of the foregoing, it is submitted that the present application is in condition for allowance and a notice to that effect is respectfully requested. However, if any issue remains after considering this response, the Examiner is invited to call the undersigned to expedite the prosecution and work out any such issue by telephone.

Respectfully submitted,



Jeffrey L. Costellia  
Registration No. 35,483

NIXON PEABODY LLP  
401 9th Street, N.W., Suite 900  
Washington, D.C. 20004-2128  
(202) 585-8000  
(202) 585-8080 (Fax)  
Customer No. 22204

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